Claims 1-24 (canceled)

25. (currently amended) A coating for a substrate consisting essentially of ~~comprising~~ a transparent Si_3N_4 or SiN_x layer applied directly on the substrate, a semimetallic layer above the Si_3N_4 or SiN_x layer, a further Si_3N_4 or SiN_x layer, and a dielectric oxide layer selected from the group consisting of Al_2O_3, SnO, Nb_2O_5, TiO_2 and SiO_2, wherein the dielectric oxide layer is disposed on the semimetallic layer, and the further Si_3N_4 layer is disposed on the dielectric oxide layer.

26. (currently amended) The coating for a substrate as claimed in claim 25, wherein the semimetallic layer comprises a CrN, NiCrN or NiCrO layer.

27. (previously presented)The coating for a substrate as claimed in claim 25, wherein a dielectric oxide layer is provided between the transparent Si_3N_4 or SiN_x layer and the semimetallic layer.

28. (previously presented)The coating for a substrate as claimed in claim 25, wherein x is a number smaller than 4/3.

29. (canceled)

30. (currently amended) A coating for a substrate as claimed in claim 25, wherein the transparent Si_3N_4 or ~~substoichiometric~~ SiN_x layers have each a layer thickness of 20 to 120 nm.

31. (previously presented)A coating for a substrate as claimed in claim 25, wherein the dielectric oxide layers have each a layer thickness of 4 to 120 nm.

32. (previously presented)A coating for a substrate as claimed in claim 25, wherein the semimetallic NiCrN, CrN or $NiCrO_x$ layers have a layer thickness of 5 to 40 nm.

33. (previously presented)A coating for a substrate as claimed in claim 25, wherein said substrate is glass.

34. (previously presented)A coating for a substrate as claimed in claim 25, wherein said substrate is a synthetic material.

35. (canceled)

36. (new) A coating for a substrate consisting essentially of a transparent Si_3N_4 or SiN_x layer applied directly on the substrate, a semimetallic layer above the Si_3N_4 or SiN_x layer, a further Si_3N_4 or SiN_x layer, and a dielectric oxide layer selected from the group consisting of Al_2O_3, SnO, Nb_2O_5, TiO_2 and SiO_2, wherein the dielectric oxide layer is disposed on the semimetallic layer, and the further Si_3N_4 layer is disposed on the dielectric oxide layer, wherein the coating comprises additional layers comprising Cr, Ni or NiCr.